











SN65HVDA1050A-Q1

SLLS994B-FEBRUARY 2010-REVISED JULY 2015

SN65HVDA1050A-Q1 EMC-Optimized High-Speed CAN Bus Transceiver

Features

- Qualified for Automotive Applications
- Meets or Exceeds the Requirements of ISO 11898-2
- GIFT/ICT Compliant
- ESD Protection up to ±12 kV (Human-Body Model) on Bus Pins
- High Electromagnetic Compliance (EMC)
- SPLIT (V_{RFF}) Voltage Source for Common-Mode Stabilization of Bus Through Split Termination
- Digital Inputs Compatible With 3.3-V and 5-V Microprocessors
- **Protection Features**
 - Bus-Fault Protection of -27 V to 40 V
 - TXD Dominant Time-Out
 - Thermal Shutdown Protection
 - Power-Up and Power-Down Glitch-Free Bus Inputs and Outputs

2 Applications

- GMW3122 Dual-Wire CAN Physical Layer
- SAE J2284 High-Speed CAN for Automotive **Applications**
- SAE J1939 Standard Data Bus Interface
- ISO 11783 Standard Data Bus Interface
- NMEA 2000 Standard Data Bus Interface

3 Description

The SN65HVDA1050A-Q1 meets or exceeds the specifications of the ISO 11898 standard for use in applications employing a controller area network (CAN). The device is qualified for use in automotive applications. As a CAN bus transceiver, this device provides differential transmit capability to the bus and differential receive capability to a CAN controller at signaling rates up to 1 megabit per second (Mbps). The signaling rate of a line is the number of voltage transitions that are made per second expressed in bits per second (bps).

The SN65HVDA1050A-Q1 device is designed for operation in especially harsh environments and includes many device protection features such as undervoltage lockout, overtemperature shutdown, wide common-mode range, and loss of ground protection. The bus pins are also protected against external cross-wiring, shorts to sources from -27 V to 40 V, and voltage transients according to ISO 7637.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)	
SN65HVDA1050A-Q1	SOIC (8)	4.90 mm × 3.91 mm	

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Block Diagram

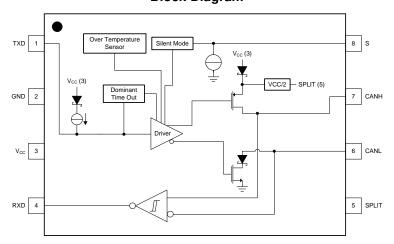




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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

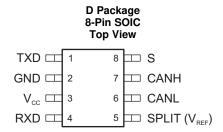
Changes from Revision A (December 2010) to Revision B

Page

Added Pin Configuration and Functions section, ESD Ratings table, Switching Characteristics table, Power Dissipation Characteristics table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation



5 Pin Configuration and Functions



Pin Functions

	PIN		DESCRIPTION
NO.	NAME	ITPE	DESCRIPTION
1	TXD	I	CAN transmit data input (low for dominant bus state, high for recessive bus state)
2	GND	GND	Ground connection
3	V_{CC}	Supply	Transceiver 5-V supply voltage input
4	RXD	0	CAN receiver data output (low in dominant bus state, high in recessive bus state)
5	SPLIT (V _{REF})	0	Common-mode stabilization output for split termination
6	CANL	I/O	LOW-level CAN bus line
7	CANH	I/O	HIGH-level CAN bus line
8	S	ļ	Silent mode select pin (active-high)



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
V _{CC}	Supply voltage ⁽²⁾	-0.3	6	V
	Voltage at any bus terminal [CANH, CANL, SPLIT (V _{REF})]	-27	40	٧
Io	Receiver output current		20	mA
V_{I}	Voltage input, ISO 7637 transient pulse (3) (CANH, CANL)	-150	100	V
V_{I}	Voltage input (TXD, S)	-0.3	6	V
T_{J}	Junction temperature	-40	150	°C
T _{stg}	Storage temperature	-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2) All voltage values, except differential I/O bus voltages, are with respect to the network ground terminal.

6.2 ESD Ratings

	-			VALUE	UNIT
	Electrostatic discharge	Human body model (HBM), per AEC Q100-	Bus pins ⁽²⁾ : Pin 7 (CANH) and Pin 6 (CANL)	±12000	
		002 ⁽¹⁾	Pin 5 [SPLIT (V _{REF})] ⁽³⁾	±10000	
V			All pins	±4000	V
V _(ESD)		Charged-device model (CDM), per AEC Q100-011		±1500	V
		Machine model ⁽⁴⁾		±200	
		IEC 61400-4-2 according to IBEE CAN EMC test specification	Bus pins to GND: Pin 7 (CANH) and Pin 6 (CANL)	±7000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.
- (2) Test method based upon JEDEC Standard 22 Test Method A114F and AEC-Q100-002, CANH and CANL bus pins stressed with respect to each other and GND.
- 3) Test method based upon JEDEC Standard 22 Test Method A114F and AEC-Q100-002, SPLIT pin stressed with respect to GND.
- (4) Tested in accordance JEDEC Standard 22, Test Method A115A.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		4.75	5.25	V
V _I or V _{IC}	Voltage at any bus terminal (separately or common mode	9)	-12	12	V
V _{IH}	High-level input voltage	TXD, S	2	5.25	V
V _{IL}	Low-level input voltage	TXD, S	0	0.8	V
V _{ID}	Differential input voltage		-6	6	V
	I Pada Januari and a salarah an marak	Driver	-70		
ГОН	High-level output current	Receiver (RXD)	-2		mA
	Law L	Driver		70	
IOL	Low-level output current	Receiver (RXD)	2		mA
T _A	Operating free-air temperature	See Power Dissipation Characteristics	-40	125	°C

⁽³⁾ Tested in accordance with ISO 7637 test pulses 1, 2, 3a, 3b per IBEE system level test (Pulse 1 = -100 V, Pulse 2 = 100 V, Pulse 3a = -150 V, Pulse 3b = 100 V). If DC may be coupled with AC transients, externally protect the bus pins within the absolute maximum voltage range at any bus terminal. This device has been tested with DC bus shorts to 40 V with leading common-mode chokes. If common-mode chokes are used in the system and the bus lines may be shorted to DC, ensure that the choke type and value in combination with the node termination and shorting voltage either do not create inductive flyback outside of voltage maximum specification or use an external transient-suppression circuit to protect the transceiver from the inductive transients.



6.4 Thermal Information

			SN65HVDA1050A-Q1	
	THERMAL METRI	C ⁽¹⁾	D (SOIC)	UNIT
			8 PINS	
П	Junction-to-ambient thermal resistance	Low-K thermal resistance (2)	211	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance	High-K thermal resistance ⁽²⁾	109	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance		49.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance		50.3	°C/W
ΨЈТ	Ψ _{JT} Junction-to-top characterization parameter		8	°C/W
ΨЈВ	Ψ _{JB} Junction-to-board characterization parameter		49.6	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance		49.2	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

over recommended operating conditions, T_A = -40 to 125°C (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
SUPPLY						'	
		Silent mode	S at V _{CC} , V _I = V _{CC}		6	10	
I _{CC}	5-V supply current	Dominant	$V_I = 0 \text{ V}, 60-\Omega \text{ load}, S = 0 \text{ V}$		50	70	mA
		Recessive	V _I = V _{CC} , No load, S = 0 V		6	10	
UV _{CC}	Undervoltage reset thresho	old		2.8		4	V
DRIVER							
V _{O(D)}	Bus output voltage	CANH	$V_I = 0$ V, $S = 0$ V, $R_L = 60$ Ω (see Figure 3 and Figure 14)	2.9	3.4	4.5	V
-(-)	(dominant)	CANL	0.8	0.85	1.2	1.5	
V _{O(R)}	Bus output voltage (recess	sive)	$V_I=3~V,~S=0~V,~R_L=60~\Omega$ (see Figure 3 and Figure 14)	2	2.3	3	V
V	Differential output voltage (dominant)		$V_I = 0$ V, $R_L = 60$ Ω , $S = 0$ V (see Figure 3, Figure 14, and Figure 4)	1.5		3	V
$V_{OD(D)}$			$V_I = 0$ V, $R_L = 45$ Ω , $S = 0$ V (see Figure 3, Figure 14, and Figure 4)	1.4		3	V
$V_{OD(R)}$	Differential output voltage	(recessive)	$V_1 = 3 V$, $S = 0 V$ (see Figure 3 and Figure 14)	-0.012		0.012	V
()	3 - ($V_I = 3 V$, $S = 0 V$, No Load	-0.5		0.05	1
V _{OC(ss)}	Steady-state common-mod	de output voltage	S = 0 V (see Figure 9)	2	2.3	3	V
$\Delta V_{OC(ss)}$	Change in steady-state co output voltage	mmon-mode	S = 0 V (see Figure 9)		30		mV
V_{IH}	High-level input voltage, T	XD input		2			V
V_{IL}	Low-level input voltage, TX	(D input				0.8	V
I _{IH}	High-level input current, TX	KD input	V _I at V _{CC}	-2		2	μΑ
I _{IL}	Low-level input current, TX	(D input	V _I at 0 V	-50		-10	μΑ
$I_{O(off)}$	Power-off TXD output curr	ent	V _{CC} at 0 V, TXD at 5 V			1	μΑ

⁽¹⁾ All typical values are at 25°C with a 5-V supply.

⁽²⁾ Tested in accordance with the low-K (EIA/JESD51-3) or high-K (EIA/JESD51-7) thermal metric definitions for leaded surface-mount packages.



Electrical Characteristics (continued)

over recommended operating conditions, $T_A = -40$ to 125°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
DRIVER ((continued)					
		V _{CANH} = -12 V, CANL open (see Figure 12)	-105	-72		
		V _{CANH} = 12 V, CANL open (see Figure 12)		0.36	1	
		$V_{CANL} = -12 \text{ V}$, CANH open (see Figure 12)	-1	-0.5		
$I_{OS(ss)}$	Short-circuit steady-state output current, dominant	V _{CANL} = 12 V, CANH open (see Figure 12)		71	105	mA
		V _{CANH} = 0 V, CANL open, TXD = low, (see Figure 12)	-100	-70		
		V _{CANL} = 32 V, CANH open, TXD = low, (see Figure 12		75	140	
	Short-circuit steady-state output current,	$-20 \text{ V} \le \text{V}_{\text{CANH}} \le 32 \text{ V}, \text{ CANL open},$ TXD = high (see Figure 12)	-15		15	mA
I _{OS(ss)}	recessive	$-20 \text{ V} \le \text{V}_{\text{CANL}} \le 32 \text{ V}, \text{ CANH open},$ TXD = high (see Figure 12)	-15		15	IIIA
Co	Output capacitance	See receiver input capacitance				
RECEIVE	ER					
V_{IT+}	Positive-going input threshold voltage	S = 0 V (see Table 1)		800	900	mV
V _{IT} _	Negative-going input threshold voltage	S = 0 V (see Table 1)	500	650		mV
V_{hys}	Hysteresis voltage $(V_{IT+} - V_{IT-})$		100	125		mV
V _{OH}	High-level output voltage	I _O = -2 mA (see Figure 7)	4	4.6		V
V _{OL}	Low-level output voltage	I _O = 2 mA (see Figure 7)		0.2	0.4	V
$I_{I(off)}$	Power-off bus input current (unpowered bus leakage current)	CANH or CANL = 5 V, Other pin at 0 V, V _{CC} at 0 V, TXD at 0 V		165	250	μΑ
I _{O(off)}	Power-off RXD leakage current	V _{CC} at 0 V, RXD at 5 V			20	μΑ
Cı	Input capacitance to ground (CANH or CANL)	TXD at 3 V, V _I = 0.4 sin (4E6πt) + 2.5 V		13		pF
C _{ID}	Differential input capacitance	TXD at 3 V, V _I = 0.4 sin (4E6πt)		6		pF
R _{ID}	Differential input resistance	TXD at 3 V, S = 0 V	30		80	kΩ
R _{IN}	Input resistance (CANH or CANL)	TXD at 3 V, S = 0 V	15	30	40	kΩ
R _{I(m)}	Input resistance matching [1 - R _{IN (CANH)} / R _{IN (CANL)})] × 100%	$V_{(CANH)} = V_{(CANL)}$	-3%	0%	3%	
S PIN					·	
V_{IH}	High-level input voltage, S input		2			V
V _{IL}	Low-level input voltage, S input				0.8	V
I _{IH}	High level input current	S at 2 V	20	40	70	μΑ
I _{IL}	Low level input current	S at 0.8 V	5	20	30	μΑ
SPLIT (V	REF) PIN					
V	Output valtage	$-50 \mu A < I_O < 50 \mu A (V_{REF})$	0.4 V _{CC}	0.5 V _{CC}	0.6 V _{CC}	V
V_O	Output voltage	–500 μA < I _O < 500 μA (SPLIT)	0.3 V _{CC}	0.5 V _{CC}	0.7 V _{CC}	V
I _{LKG}	Leakage current, unpowered	V _{CC} = 0 V, −12 V ≤ V _{SPLIT} ≤ 12 V	- 5		5	μΑ



6.6 Power Dissipation Characteristics

over recommended operating conditions, T_A = -40 to 125°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_{D}	Average power dissipation	V_{CC} = 5 V, T_{J} = 27°C, R_{L} = 60 Ω , S = 0 V, Input to TXD at 500 kHz, 50% duty cycle square wave, C_{L} at RXD = 15 pF		112		m\\/
		V_{CC} = 5.5 V, T_J = 130°C, R_L = 45 Ω , S = 0 V, Input to TXD at 500 kHz, 50% duty cycle square wave, C_L at RXD = 15 pF			170	mW
	Thermal shutdown temperature			190		°C

6.7 Switching Characteristics

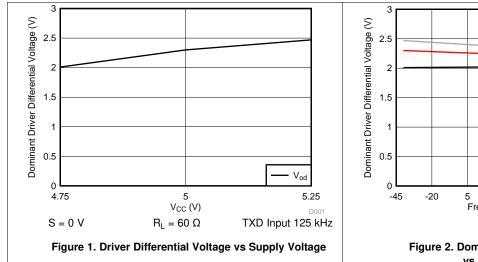
over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY			1			
t _{d(LOOP2)}	Total loop delay, driver input to receiver output, dominant to recessive	S = 0 V (see Figure 10)	90		230	ns
DEVICE S	WITCHING CHARACTERISTICS				·	
$t_{d(LOOP1)}$	Total loop delay, driver input to receiver output, recessive to dominant	S = 0 V (see Figure 10)	90		230	ns
$t_{d(LOOP2)}$	Total loop delay, driver input to receiver output, dominant to recessive	S = 0 V (see Figure 10)	90		230	ns
DRIVER S	WITCHING CHARACTERISTICS				·	
t _{PLH}	Propagation delay time, low-to-high level output	S = 0 V (see Figure 5)	25	65	120	ns
t _{PHL}	Propagation delay time, high-to-low level output	S = 0 V (see Figure 5)	25	45	120	ns
t _r	Differential output signal rise time	S = 0 V (see Figure 5)		25		ns
t _f	Differential output signal fall time	S = 0 V (see Figure 5)		50		ns
t _{en}	Enable time from silent mode to normal mode and transmission of dominant	See Figure 8			1	μs
t _(dom)	Dominant time-out ⁽¹⁾	↓V _I (see Figure 11)	300	450	700	μs
RECEIVER	SWITCHING CHARACTERISTICS				·	
t _{PLH}	Propagation delay time, low-to-high- level output	S = 0 V or V _{CC} (see Figure 7)	60	100	130	ns
t _{PHL}	Propagation delay time, high-to-low-level output	S = 0 V or V _{CC} (see Figure 7)	45	70	130	ns
t _r	Output signal rise time	S = 0 V or V _{CC} (see Figure 7)		8		ns
t _f	Output signal fall time	S = 0 V or V _{CC} (see Figure 7)		8		ns

⁽¹⁾ The TXD dominant time out, t_(dom), disables the driver of the transceiver once the TXD has been dominant longer than t_(dom), which releases the bus lines to recessive, preventing a local failure from locking the bus dominant. The driver may only transmit dominant again after TXD has been returned HIGH (recessive). Although this protects the bus from local faults, locking the bus dominant, it limits the minimum data rate possible. The CAN protocol allows a maximum of eleven successive dominant bits (on TXD) for the worst case, where five successive dominant bits are followed immediately by an error frame. This, along with the t_(dom) minimum, limits the minimum bit rate. The minimum bit rate may be calculated by: Minimum Bit Rate = 11 / t_(dom) = 11 bits / 300 μs = 37 kbps.



6.8 Typical Characteristics



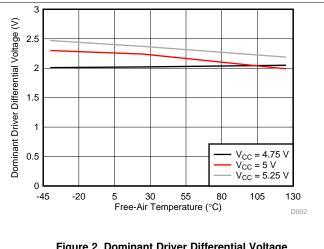


Figure 2. Dominant Driver Differential Voltage vs Free-Air Temperature



7 Parameter Measurement Information

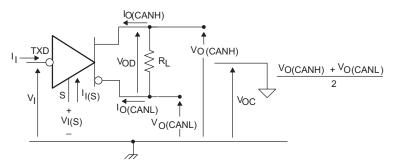


Figure 3. Driver Voltage, Current, and Test Definition

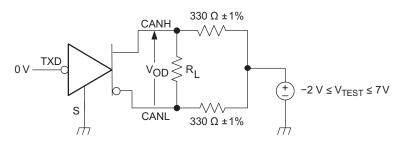
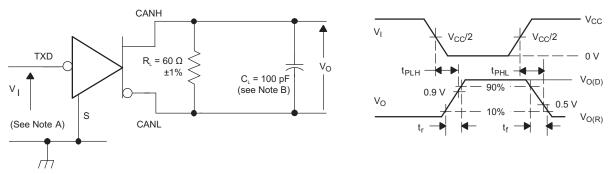


Figure 4. Driver V_{OD} Test Circuit



- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 125 kHz, 50% duty cycle, $t_r \leq$ 6 ns, $t_f \leq$ 6 ns, $Z_O =$ 50 Ω .
- B. C₁ includes instrumentation and fixture capacitance within ±20%.

Figure 5. Driver Test Circuit and Voltage Waveforms

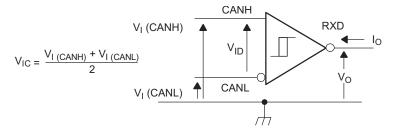
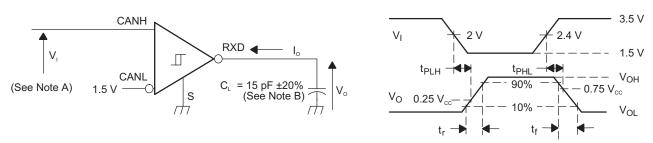


Figure 6. Receiver Voltage and Current Definitions



Parameter Measurement Information (continued)

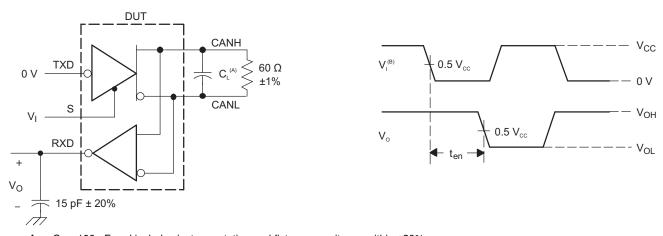


- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 125 kHz, 50% duty cycle, $t_r \leq$ 6 ns, $t_f \leq$ 6 ns, $t_G \leq$ 50 Ω .
- B. C_L includes instrumentation and fixture capacitance within ±20%.

Figure 7. Receiver Test Circuit and Voltage Waveforms

Table 1. Differential Input Voltage Threshold Test

		OUTPUT					
V _{CANH}	V _{CANL}	V _{ID}		R			
–11.1 V	–12 V	900 mV	L				
12 V	11.1 V	900 mV	L	V			
−6 V	–12 V	6 V	L	V _{OL}			
12 V	6 V	6 V	L				
–11.5 V	–12 V	500 mV	Н				
12 V	11.5 V	500 mV	Н				
-12 V	-6 V	6 V	Н	V _{OH}			
6 V	12 V	6 V	Н				
Open	Open	Х	Н				



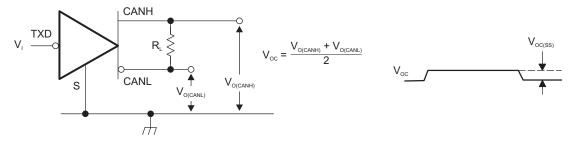
- A. $C_L = 100 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.
- B. All V_1 input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 6$ ns, pulse repetition rate (PRR) = 125 kHz, 50% duty cycle.

Figure 8. t_{en} Test Circuit and Waveforms

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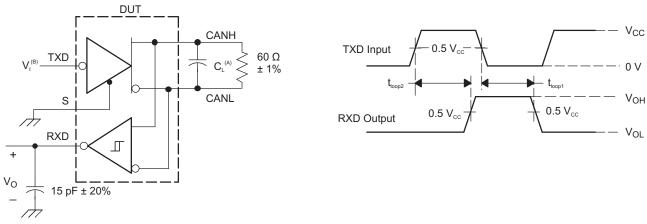
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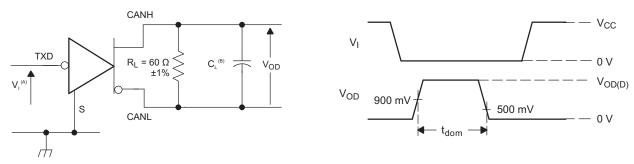
NOTE: All V_1 input pulses are from 0 V to V_{CC} and supplied by a generator having the following characteristics: t_r or $t_f \le 6$ ns, pulse repetition rate (PRR) = 125 kHz, 50% duty cycle.

Figure 9. Common-Mode Output Voltage Test and Waveforms



- A. $C_L = 100$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.
- B. All V_1 input pulses are from 0 V to V_{CC} and supplied by a generator having the following characteristics: t_r or $t_f \le 6$ ns, pulse repetition rate (PRR) = 125 kHz, 50% duty cycle.

Figure 10. t_(LOOP) Test Circuit and Waveforms



- A. All V_1 input pulses are from 0 V to V_{CC} and supplied by a generator having the following characteristics: t_r or $t_f \le 6$ ns, pulse repetition rate (PRR) = 500 Hz, 50% duty cycle.
- B. $C_L = 100 \text{ pF}$ includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 11. Dominant Time-Out Test Circuit and Waveforms



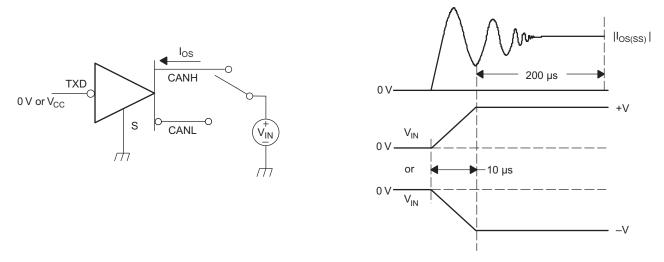


Figure 12. Driver Short-Circuit Current Test and Waveforms

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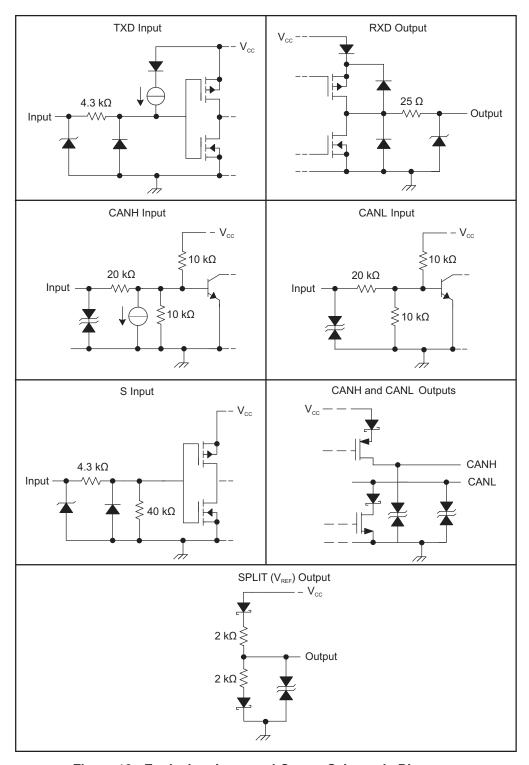


Figure 13. Equivalent Input and Output Schematic Diagrams

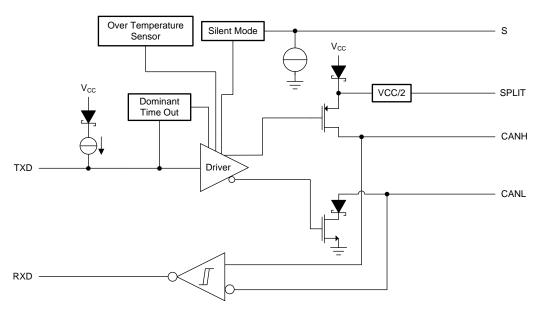


8 Detailed Description

8.1 Overview

The SN65HVDA1050A-Q1 CAN transceiver is compatible with the ISO 11898-2 high-speed controller area network (CAN) physical layer standard. The device is designed to interface between the differential bus lines in controller area network and the CAN protocol controller at data rates up to 1 Mbps.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Operating Modes

The device has two main operating modes: normal mode and silent mode. Operating mode selection is made through the S input pin.

Table 2. Operating Modes

S PIN	MODE	DRIVER	RECEIVER	RXD PIN		
LOW	Normal	Enabled (On)	Enabled (On)	Mirrors CAN bus		
HIGH	Silent	Disabled (Off)	Enabled (On)	Mirrors CAN bus		

8.3.1.1 Normal Mode

This is the normal operating mode of the device. Normal mode is selected by setting S low. The CAN driver and receiver are fully operational and CAN communication is bidirectional. The driver is translating a digital input on TXD to a differential output on CANH and CANL. The receiver is translating the differential signal from CANH and CANL to a digital output on RXD. In recessive state, the bus pins are biased to $0.5 \times V_{CC}$. In dominant state, the bus pins (CANH and CANL) are driven differentially apart. Logic high is equivalent to recessive on the bus and logic low is equivalent to a dominant (differential) signal on the bus.



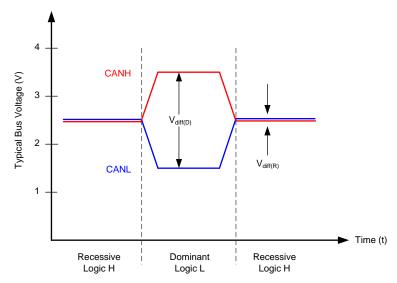


Figure 14. Bus Logic-State Voltage Definitions

The SPLIT (V_{REF}) pin is biased to 0.5 × V_{CC} for bus common mode bus voltage bias stabilization in split termination network applications (see *Application and Implementation*).

8.3.1.2 Silent Mode

Silent mode disables the driver (transmitter) of the device; however, the receiver still operates and translates the differential signal from CANH and CANL to the digital output on RXD. It is selected by setting S high. The bus pins (CANH and CANL) are biased to $0.5 \times V_{CC}$. The SPLIT (V_{REF}) pin is biased to $0.5 \times V_{CC}$.

8.3.2 Protection Features

8.3.2.1 TXD Dominant State Timeout

During normal mode operation (the only mode where the CAN driver is active), the TXD dominant time-out circuit prevents the transceiver from blocking network communication in the event of a hardware or software failure where TXD is held dominant longer than the time-out period, t_{DST} . The dominant time-out circuit is triggered by a falling edge on TXD. If no rising edge occurs before the time-out constant of the circuit expires (t_{DST}), the CAN bus driver is disabled, thus freeing the bus for communication between other network nodes. The CAN driver is reactivated when a recessive signal occurs on the TXD pin, thus clearing the dominant-state time-out. The CAN bus pins are biased to recessive level during a TXD dominant-state time-out, and SPLIT (V_{REF}) remains on.

NOTE

The maximum dominant TXD time allowed by the TXD dominant state time-out limits the minimum possible data rate of the device. The CAN protocol allows a maximum of eleven successive dominant bits (on TXD) for the worst case, where five successive dominant bits are followed immediately by an error frame. This, along with the $t_{(dom)}$ minimum, limits the minimum bit rate. The minimum bit rate may be calculated by:

Minimum Bit Rate = $11 / t_{(dom)}$

8.3.2.2 Thermal Shutdown

If the junction temperature of the device exceeds the thermal-shutdown threshold, the device turns off the CAN driver circuits. The SPLIT (V_{REF}) pin remains biased. This condition is cleared when the temperature drops below the thermal-shutdown temperature of the device.

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Product Folder Links: SN65HVDA1050A-Q1



8.3.2.3 Undervoltage Lockout and Unpowered Device

The device has undervoltage detection and lockout on the V_{CC} supply. If an undervoltage condition is detected on V_{CC} , the device protects the bus.

The TXD pin is pulled up to V_{CC} to force a recessive input level if the pin floats. The S pin is pulled up to GND to force the device into normal mode if the pin floats.

The bus pins [CANH, CANL, and SPLIT (V_{REF})] all have low leakage currents when the device is unpowered.

8.4 Device Functional Modes

Table 3. Driver Function Table (1)

INP	UTS	OUTP	BUS STATE	
TXD	S	CANH	CANL	DUS STATE
L	L or Open	Н	L	Dominant
Н	X	Z Z		Recessive
Open	X	Z	Z	Recessive
Х	Н	Z	Z	Recessive

(1) H = high level, L = low level, X = irrelevant, ? = indeterminate, Z = high impedance

Table 4. Receiver Function Table⁽¹⁾

DIFFERENTIAL INPUTS V _{ID} = V(CANH) - V(CANL)	OUTPUT RXD	BUS STATE		
V _{ID} ≥ 0.9 V	L	Dominant		
$0.5 \text{ V} < \text{V}_{\text{ID}} < 0.9 \text{ V}$?	?		
V _{ID} ≤ 0.5 V	Н	Recessive		
Open	Н	Recessive		

(1) H = high level, L = low level, X = irrelevant, ? = indeterminate, Z = high impedance



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

9.1.1 Using the Device With 3.3-V Microcontrollers

The input level threshold for the digital input pins of this device is 3.3-V compatible; however, a few application considerations must be taken when using this device with 3.3-V microcontrollers. The TXD input pin has an internal pullup source to V_{CC} . Some microcontroller vendors recommend using an open-drain configuration on their I/O pins in this case, even though the pullup limits the current. As such, care must be taken at the application level that TXD has sufficient pullup to meet system timing requirements for CAN. The internal pullup on TXD especially may not be sufficient to overcome the parasitic capacitances and allow for adequate CAN timing; thus, an additional external pullup may be required. Care must also be taken with the RXD pin of the microcontroller, as the RXD output of this device drives the full V_{CC} range (5 V). If the microcontroller RXD input pin is not 5-V tolerant, this must be addressed at the application level. Other options include using a CAN transceiver from Texas Instruments with I/O level adapting or a 3.3-V CAN transceiver.

9.1.2 Using SPLIT (V_{REF}) With Split Termination

The SPLIT (V_{REF}) pin voltage output provides $0.5 \times V_{CC}$ in normal mode. This pin is specified for both the SPLIT sink/source current condition and the V_{REF} sink/source current condition. The circuit may be used by the application to stabilize the common-mode voltage of the bus by connecting it to the center tap of split termination for the CAN network (see Figure 15). The SPLIT (V_{REF}) pin provides a stabilizing recessive voltage drive to offset leakage currents of unpowered transceivers or other bias imbalances that might bring the network common-mode voltage away from $0.5 \times V_{CC}$. Using this feature in a CAN network improves the electromagnetic-emissions behavior of the network by eliminating fluctuations in the bus common-mode voltage levels at the start of message transmissions.

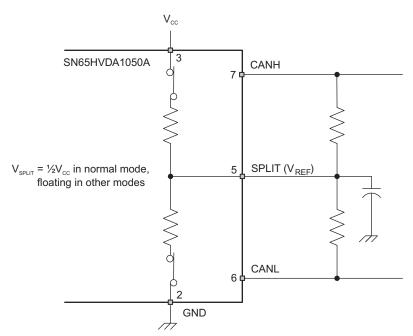


Figure 15. SPLIT Pin Stabilization Circuitry and Application



9.2 Typical Application

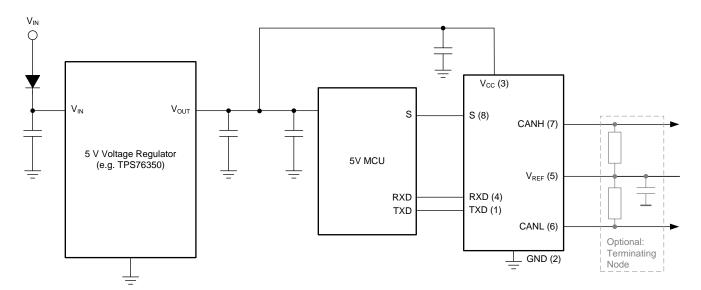


Figure 16. Typical Application Using Split Termination for Stabilization

9.2.1 Design Requirements

9.2.1.1 Bus Loading, Length, and Number of Nodes

The ISO 11898 Standard specifies up to 1-Mbps data rate, a maximum bus length of 40 meters, a maximum drop-line (stub) length of 0.3 meters, and a maximum of 30 nodes. However, with careful network design, the system may have longer cables, longer stub lengths, and many more nodes to a bus. Many CAN organizations and standards have scaled the use of CAN for applications outside the original ISO 11898 standard. They have made system-level trade-offs for data rate, cable length, and parasitic loading of the bus. Examples of some of these specifications are ARINC825, CANopen, CAN Kingdom, DeviceNet, and NMEA200 (see Figure 17).

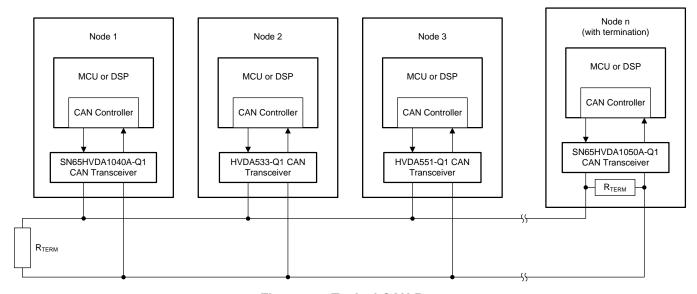


Figure 17. Typical CAN Bus



Typical Application (continued)

A high number of nodes requires a transceiver with high input impedance and wide common-mode range, such as the SN65HVDA1050A-Q1 CAN transceiver. ISO 11898-2 specifies that the driver differential output with a 60- Ω load (two 120- Ω termination resistors in parallel) and the differential output must be greater than 1.5 V. The SN65HVDA1050A-Q1 device is specified to meet the 1.5-V requirement with a 60- Ω load, and additionally specified with a differential output voltage minimum of 1.2 V across a common-mode range of -2 V to 7 V through a 330- Ω coupling network. This network represents the bus loading of 90 SN65HVDA1050A-Q1 transceivers based on their minimum differential input resistance of 30 k Ω . Therefore, the SN65HVDA1050A-Q1 supports up to 90 transceivers on a single bus segment with margin to the 1.2-V minimum differential input voltage requirement at each node.

For CAN network design, margin must be given for signal loss across the system and cabling, parasitic loadings, network imbalances, ground offsets, and signal integrity; thus the practical maximum number of nodes may be lower. Bus length may also be extended beyond the original ISO 11898 standard of 40 meters by careful system design and data rate tradeoffs. For example, CANopen network design guidelines allow the network to be up to 1-km with changes in the termination resistance, cabling, less than 64 nodes, and a significantly lowered data rate.

This flexibility in CAN network design is one of the key strengths of the various extensions and additional standards that have been built on the original ISO 11898 CAN standard.

9.2.1.2 CAN Termination

The ISO 11898 standard specifies the interconnect to be a twisted-pair cable (shielded or unshielded) with $120-\Omega$ characteristic impedance (Z_O). Resistors equal to the characteristic impedance of the line must be used to terminate both ends of the cable to prevent signal reflections. Unterminated drop lines (stubs) connecting nodes to the bus must be kept as short as possible to minimize signal reflections. The termination may be on the cable or in a node, but if nodes may be removed from the bus, the termination must be carefully placed so it is not removed from the bus.

Termination is typically a $120-\Omega$ resistor at each end of the bus. If filtering and stabilization of the common-mode voltage of the bus is desired, then split termination may be used (see Figure 18 and *Using SPLIT* (V_{REF}) *With Split Termination*).

Care must be taken when determining the power ratings of the termination resistors. A typical worst case fault condition is when the system power supply and ground are shorted across the termination resistance, which results in much higher current through the termination resistance than the current limit of the CAN transceiver.

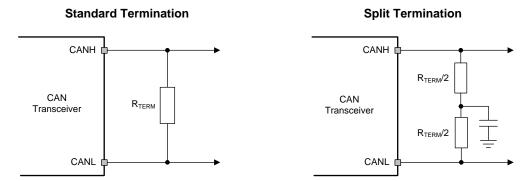


Figure 18. CAN Termination Scheme

9.2.1.3 Loop Propagation Delay

Transceiver loop delay is a measure of the overall device propagation delay, consisting of the delay from the driver input (the TXD pin) to the differential outputs (the CANH and CANL pins), plus the delay from the receiver inputs (the CANH and CANL) to its output (the RXD pin). A typical loop delay for the SN65HVDA1050A-Q1 transceiver is displayed in Figure 20 and Figure 21.



Typical Application (continued)

9.2.2 Detailed Design Procedure

9.2.2.1 ESD Protection

A typical application that employs a CAN-bus network may require some form of ESD, burst, and surge protection to shield the CAN transceiver against unwanted transients, which could cause potential damage to the transceiver. To help shield the SN65HVDA1050A-Q1 transceiver against these high energy transients, transient voltage suppressors can be implemented on the CAN differential bus terminals. These devices help to absorb the impact of an ESD, burst, and/or surge strike.

9.2.2.2 Transient Voltage Suppresser (TVS) Diodes

Transient voltage suppressors are the preferred protection components for a CAN bus due to their low capacitance, which allows for design into every node of a multi-node network without requiring a reduction in data rate (see Figure 19). With response times of a few picoseconds and power ratings of up to several kilowatts, TVS diodes present the most effective protection against ESD, burst, and surge transients.

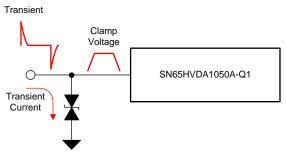
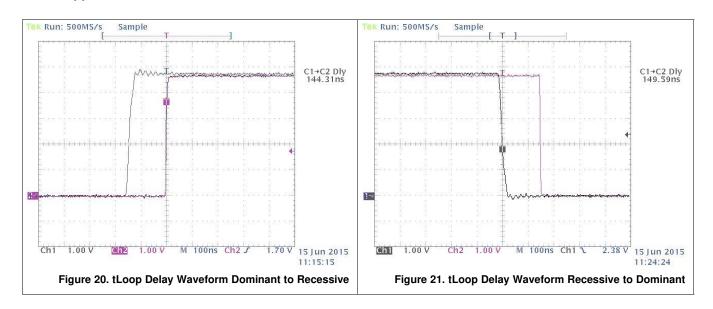


Figure 19. Transcient

9.2.3 Application Curves





10 Power Supply Recommendations

To ensure reliable operation at all data rates and supply voltages, each supply must be decoupled with a 100-nF ceramic capacitor located as close as possible to the V_{CC} supply pins. One option is the TPS76350 device, which is a linear voltage regulator that is suitable for the 5-V supply rail.

11 Layout

11.1 Layout Guidelines

In order for the PCB design to be successful, start with a design of the protection and filtering circuitry. Because ESD and EFT transients have a wide frequency bandwidth from approximately 3 MHz to 3 GHz, high-frequency layout techniques must be applied during PCB design. On-chip IEC ESD protection is good for laboratory and portable equipment, but it is usually not sufficient for EFT and surge transients occurring in industrial environments. Therefore, robust and reliable bus node design requires the use of external transient protection devices at the bus connectors. Placement at the connector also prevents these harsh transient events from propagating further into the PCB and system.





High-frequency current follows the path of least inductance and not the path of least resistance.

Design the bus protection components in the direction of the signal path. Do not force the transient current to divert from the signal path to reach the protection device. An example placement of the transient voltage suppressor (TVS) device indicated as D1 (either bidirectional diode or varistor solution) and bus filter capacitors C5 and C7 are shown in Figure 22.

The bus transient protection and filtering components must be placed as close to the bus connector, J1, as possible. This prevents transients, ESD and noise from penetrating onto the board and disturbing other devices.

Bus termination: Figure 22 shows split termination, which is where the termination is split into two resistors, R5 and R6, with the center or split tap of the termination connected to ground through capacitor C6. Split termination provides common-mode filtering for the bus. When termination is placed on the board instead of directly on the bus, care must be taken to ensure that the terminating node is not removed from the bus because this causes signal integrity issues if the bus is not properly terminated on both ends. Bypass and bulk capacitors must be placed as close as possible to the supply pins of transceiver, examples include C2 and C3 (V_{CC}).

Use at least two vias for V_{CC} and ground connections of bypass capacitors and protection devices to minimize trace and via inductance.

To limit the current of digital lines, serial resistors may be used. Examples are R1, R2, R3, and R4.

To filter noise on the digital I/O lines, a capacitor may be used close to the input side of the I/O as shown by C1 and C4.

Because the internal pullup and pulldown biasing of the device is weak for floating pins, an external $1-k\Omega$ to $10-k\Omega$ pullup or pulldown resistor must be used to bias the state of the pin more strongly against noise during transient events.

Pin 1: If an open-drain host processor is used to drive the TXD pin of the device, an external pullup resistor between 1 k Ω and 10 k Ω must be used to drive the recessive input state of the device.

Pin 5: SPLIT must be connected to the center point of a split termination scheme to help stabilize the common-mode voltage to V_{CC} / 2. If SPLIT is unused, it must be left floating.

Pin 8: Is shown assuming the mode pin, STB, is used. If the device is only to be used in normal mode, R3 is not needed, and the pads of C4 could be used for the pulldown resistor to GND



11.2 Layout Example

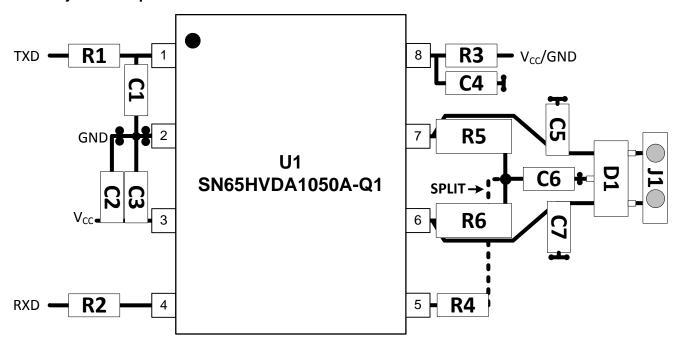


Figure 22. Layout



12 Device and Documentation Support

12.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Lise

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.2 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN65HVDA1050AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A1050A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

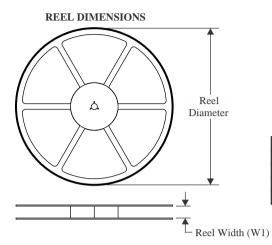
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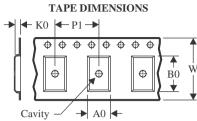
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

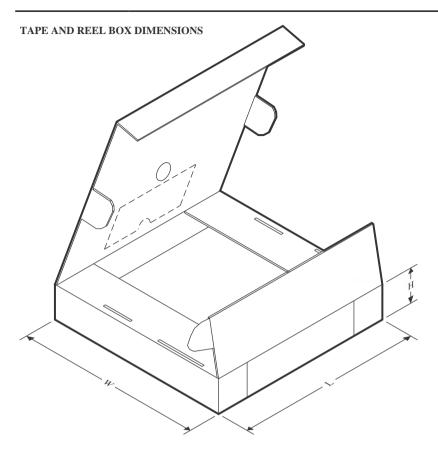


*All dimensions are nominal

Device	U	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVDA1050AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN65HVDA1050AQDRQ1	SOIC	D	8	2500	356.0	356.0	35.0	

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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